

PDFN56

Pin Definition:

- | | |
|-----------|----------|
| 1. Source | 8. Drain |
| 2. Source | 7. Drain |
| 3. Source | 6. Drain |
| 4. Gate | 5. Drain |

Note:

MSL 1 (Moisture Sensitivity Level)
per J-STD-020

TSM055N03EPQ56

30V N-Channel MOSFET

Key Parameter Performance

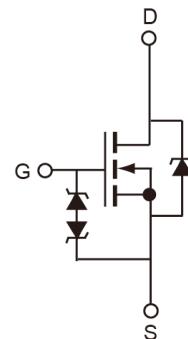
Parameter	Value	Unit
V_{DS}	30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	5.5
	$V_{GS} = 4.5V$	8.5
Q_g	11.1	nC

Ordering Information

Part No.	Package	Packing
TSM055N03EPQ56 RLG	PDFN56	2.5kpcs / 13" Reel

- Note:** Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET with ESD protection

Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $T_c = 25^\circ\text{C}$	I_D	80	A
$T_c = 100^\circ\text{C}$		51	
Drain Current-Pulsed ^(Note 1)	I_{DM}	320	A
Single Pulse Avalanche Energy ^(Note 2)	E_{AS}	45	mJ
Maximum Power Dissipation @ $T_c = 25^\circ\text{C}$	P_D	74	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\theta JC}$	1.7	°C/W
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	62	°C/W

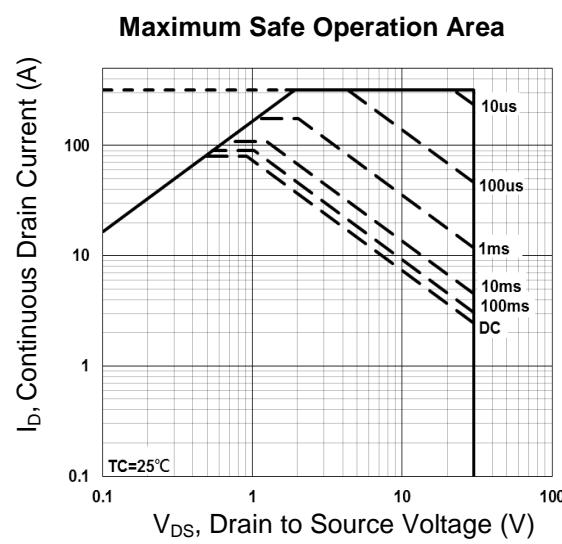
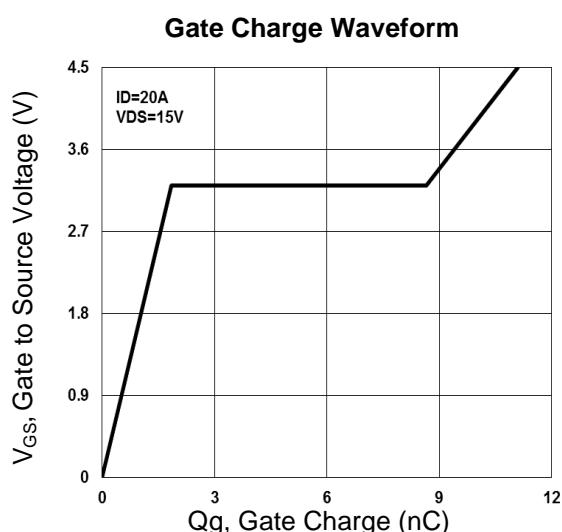
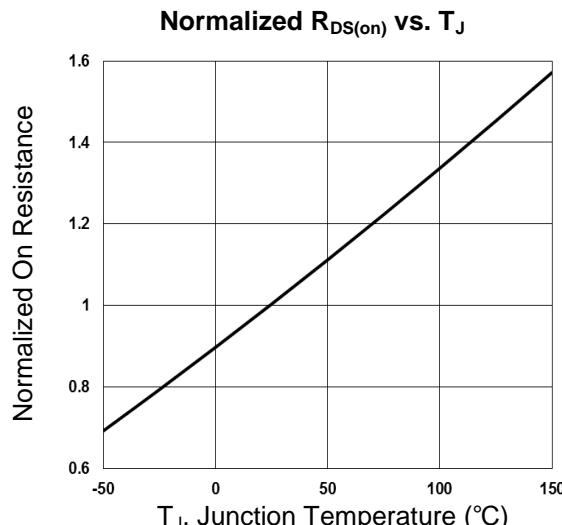
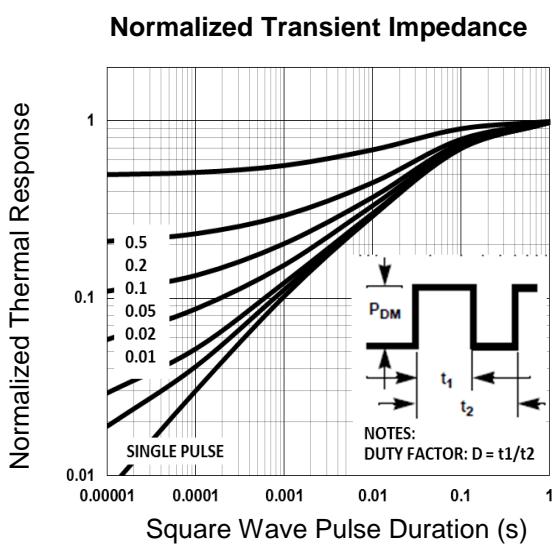
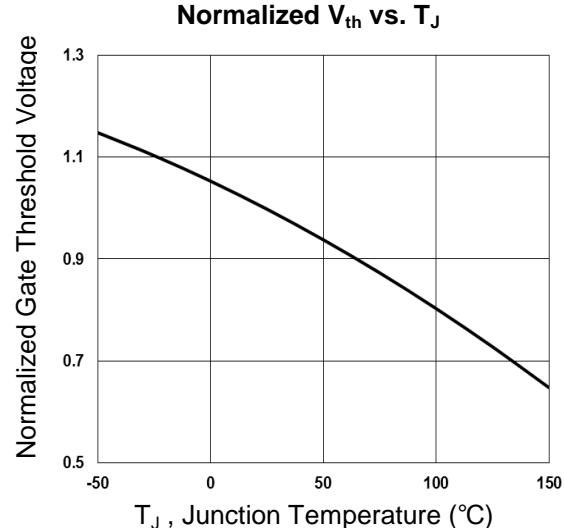
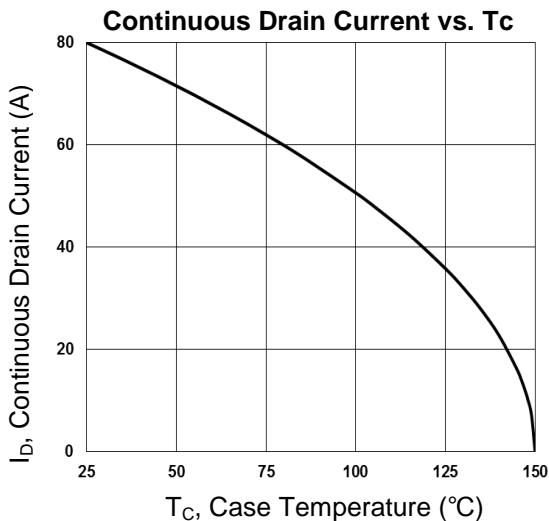
Electrical Specifications ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	30	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	$R_{DS(ON)}$	--	4.5	5.5	$\text{m}\Omega$
	$V_{GS} = 4.5\text{V}, I_D = 10\text{A}$			6.3	8.5	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(\text{TH})}$	1.2	1.6	2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$	I_{DSS}	--	--	1	μA
	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$		--	--	10	μA
Gate Body Leakage	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 10	μA
Dynamic						
Total Gate Charge ^(Note 3,4)	$V_{DS} = 15\text{V}, I_D = 20\text{A}, V_{GS} = 4.5\text{V}$	Q_g	--	11.1	--	nC
Gate-Source Charge ^(Note 3,4)		Q_{gs}	--	1.85	--	
Gate-Drain Charge ^(Note 3,4)		Q_{gd}	--	6.8	--	
Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	1210	--	pF
Output Capacitance		C_{oss}	--	190	--	
Reverse Transfer Capacitance		C_{rss}	--	100	--	
Switching						
Turn-On Delay Time ^(Note 3,4)	$V_{GS} = 10\text{V}, V_{DS} = 15\text{V}, R_G = 3.3\Omega, I_D = 15\text{A}$	$t_{d(on)}$	--	7.5	--	ns
Turn-On Rise Time ^(Note 3,4)		t_r	--	14.5	--	
Turn-Off Delay Time ^(Note 3,4)		$t_{d(off)}$	--	35.2	--	
Turn-Off Fall Time ^(Note 3,4)		t_f	--	9.6	--	
Drain-Source Diode Characteristics and Maximum Rating						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I_S	--	--	80	A
Maximum Pulse Drain-Source Diode Forward Current		I_{SM}	--	--	320	A
Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 1\text{A}$	V_{SD}	--	--	1	V

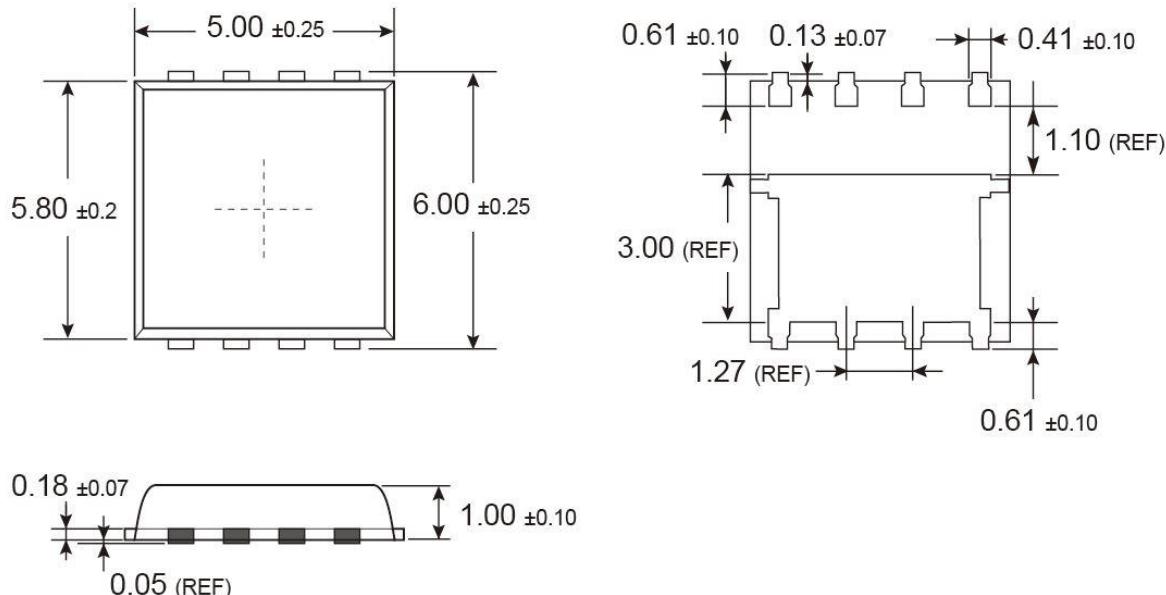
Notes:

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD} = 25\text{V}, V_{GS} = 10\text{V}, L = 0.1\text{mH}, I_{AS} = 42\text{A}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.
3. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
4. Essentially independent of operating temperature.

Electrical Characteristics Curves



PDFN56 Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
(**O**=Jan, **P**=Feb, **Q**=Mar, **R**=Apr, **S**=May, **T**=Jun, **U**=Jul, **V**=Aug, **W**=Sep,
X=Oct, **Y**=Nov, **Z**=Dec)
- L** = Lot Code



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